Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

1-15. (canceled)

16. (currently amended) A ~~semiconductor die assembled into a packaged~~ semiconductor device ~~by a method~~ comprising:

a semiconductor die;

~~dispensing a die attach material onto~~ a chip carrier;

~~, wherein the~~ a die attach material ~~comprises~~ including a component of which the CTE is negative ~~negative CTE material~~; and

~~attaching a~~ the semiconductor die attached to the chip carrier with [[to]] the die attach material.

17. (currently amended) The semiconductor [[die]] device of claim 16, wherein ~~dispensing the die attach material onto~~ the chip carrier ~~further comprises dispensing the die attach material onto a structure~~ is selected from a group consisting of a ~~package~~ substrate and a leadframe.

18. (currently amended) The semiconductor [[die]] device of claim [[17]] 16, wherein ~~dispensing a die attach material comprising a~~ the component with negative-CTE ~~material further comprises dispensing a die attach material comprising a~~ is a tungstate material.

19. (original) The semiconductor [[die]] device of claim 16, ~~wherein the method further comprises encapsulating the semiconductor die with~~ further comprising an encapsulant that

encapsulates the semiconductor die, the encapsulant including a component of ~~comprising a~~ negative-CTE ~~material~~.

20. (currently amended) The semiconductor [[die]] device of claim 19, wherein ~~encapsulating the semiconductor die with an encapsulant comprising a negative-CTE material further comprises encapsulating the semiconductor die with an encapsulant comprising a~~ the encapsulant includes a tungstate material.

21. (currently amended) The semiconductor [[die]] device of claim 19, wherein ~~encapsulating the semiconductor die with an~~ the encapsulant ~~further comprises encapsulating the semiconductor die with a material~~ is selected from a group consisting of a mold compound and a glob-top material.

22. (currently amended) A semiconductor ~~die assembled into a packaged semiconductor~~ device ~~by a method~~ comprising:

a semiconductor die disposed on a chip carrier;

~~dispensing~~ a lid attach material comprising a negative-CTE material disposed over ~~the inactive~~ a surface of a semiconductor die and ~~around at least~~ a portion of ~~a perimeter of the upper surface of a package substrate~~ the chip carrier; and

~~adhering a package~~ a lid adhered to the lid attach material.

23. (currently amended) The ~~method~~ semiconductor device of claim 22, wherein [[dispensing]] the lid attach material ~~comprising a negative-CTE material further comprises dispensing a lid attach material comprising~~ includes a tungstate material.

24. (currently amended) The ~~method~~ semiconductor device of claim 23, wherein ~~dispensing the lid attach material comprising a~~ the tungstate material ~~further comprises dispensing a lid attach material comprising a material~~ is selected from a group consisting of zirconium tungstate, halfnium tungstate, and a solution of zirconium and halfnium tungstate.

25. (new) The semiconductor of claim 19, in which the die attaching material and the encapsulant include a component selected from a group consisting of zirconium tungstate, halfnium tungstate, and a solution of zirconium and halfnium tungstate.